

CALIFORNIA MICRO DEVICES



2 CHANNEL ESD PROTECTION ARRAY

Features

2 channel ESD protection

PRELIMINARY

- 15KV ESD protection (HBM)
- 8KV contact, 15KV air ESD protection per IEC 1000-4-2
- Low loading capacitance, 3 pF typ.
- Miniature 4-pin SOT-143 package

Applications

- I/O port: protection for cellular phones, notebooks computers, PDA, etc.
- ESD protection for sensitive electronic equipment.
- ESD protection for applications where low capacitive loading is required.

Product Description

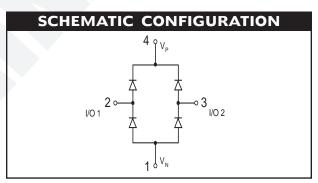
The PAC DN004™ is a diode array designed to provide two channels of ESD protection for electronic components or sub-systems. Each channel consists of a pair of diodes which steers the ESD current pulse either to the positive (V₀) or negative (V_N) supply. The PAC DN004 will protect against ESD pulses up to 15 KV Human Body Model, and 8KV contact discharge per International Standard IEC1000-4-2.

This device has identical characteristics as the PAC DN006 (6 channel array). They can be used together in order to provide a larger number of protected inputs if required. This device is particularly well-suited for portable electronics (e.g. cellular phones, PDAs, notebook computers) because of its small package footprint, high ESD protection level, and low loading capacitance. It is also suitable for protecting video output lines and I/O ports in computers and peripheral equipment.

ABSOLUTE MAXIMUM RATINGS

Diode Forward DC Current (Note 1) 20mA Storage Temperature -65°C to 150°C Operating Temperature Range 0°C to 70°C DC Voltage at any Channel Input V_N -0.5V to V_P +0.5V

Note 1: Only one diode conducting at a time.



STANDARD SPECIFICATIONS					
Parameter	Min.	Тур.	Max.		
Operating Supply Voltage (V _P -V _N)			5.5 V		
Diode Forward Voltage, $I_F = 20$ mA, $T = 25$ °C	0.65 V		0.85 V		
Diode reverse breakdown voltage, $T = 25^{\circ}C$					
Top Diode (Cathode to V _P)	19.0 V				
Bottom Diode (Anode to V _N)	28.0 V				
ESD Protection					
Peak Discharge Voltage at any Channel Input, in-system (Note 2)					
Human Body Model, Method 3015 (Note 3, 4)	-15 KV		+15 KV		
Contact per IEC 1000-4-2 (Note 5)	-8KV		+8KV		
Air Discharge per IEC 1000-4-2 (Note 5)	-15KV		+15KV		
Channel Clamp Voltage @ 15KV ESD HBM, T = 25°C					
(Notes 3, 4)					
Positive transients			V _P +13.0 V		
Negative transients			V _N -13.0 V		
Channel Leakage Current, $T = 25^{\circ}C$		0.1 μΑ	1.0 μA		
Channel Input Capacitance (Measured @ 1 MHz)					
$V_{P} = 5V, V_{N} = 0V, V_{IN} = 2.5V$		3pF	6pF		
Package Power Rating			225mW		

Note 2: From I/O pins to V_P or V_N only. V_P bypassed to V_N with 0.2 μF ceramic capacitor.

Note 3: Human Body Model per MIL-STD-883, Method 3015, $C_{Discharge} = 100 pF$, $R_{Discharge} = 1.5 K\Omega$, $V_p = 5.0 V$, $V_N = GND$.

Note 4: This parameter is guaranteed by characterization only.

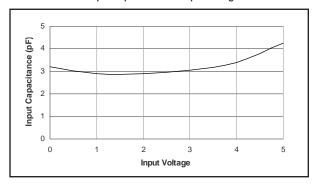
Note 5: Standard IEC1000-4-2 with $C_{Discharge} = 150pF$, and $R_{Discharge} = 330\Omega$, $V_p = 5V$, $V_N = GND$.

© 1998 California Micro Devics Corp. All rights reserved. PAC DN006™ and PAC DN004™ are trademarks of California Micro Devices Corp. California Micro Devics manufactures products covered by one or more of U.S. Pat. Nos. 5,355,014, 5,370,766, and 5,514,612 and other pending applications. © 1993, 1998 CMD Corp. All rights reserved.

C0211297D



Input Capacitance vs. Input Voltage



Typical variation of C_{IN} with V_{IN} . $(V_P=5V, V_N=0V)$

STANDARD PART ORDERING INFORMATION					
Pack	cage	Ordering Part Number			
Pins	Style	Bag	Tape & Reel	Part Marking	
4	SOT-143	PACDN004M/B	PACDN004M/R	D004	

Application Information

In order to realize the maximum protection against ESD pulses with the PAC DN004, care must be taken in the PCB layout to minimize the parasitic series inductance to the Supply and Ground rails. Refer to Figure 1, which illustrates the case of a positive ESD pulse applied between an input channel and Chassis Ground. The parasitic series inductance back to the power supply is represented by L_1 . The voltage V_Z on the line being protected is:

 V_Z = Forward voltage drop of $D_1 + L_1 \times d(I_{esd})/dt + V_{Supply}$

where I_{esd} is the ESD current pulse, and V_{Supply} is the positive supply voltage.

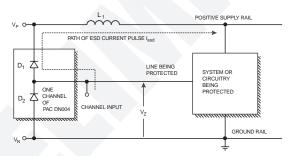


Figure 1

An ESD current pulse can rise from zero to its peak value in a very short time. As an example, consider the case of an ESD pulse that rises from zero to 10 Amps in 1nS. Here $d(l_{esd})/dt$ can be approximated by $\Delta l_{esd}/\Delta t$, or $10/(1\times10^{-9})$. So each nano Henry of series inductance (L₁) will lead to a 10V increment in V_Z.

Similarly for negative ESD pulses, parasitic series inductance from the V_N pin to the ground rail will lead to increased negative voltage on the line being protected.

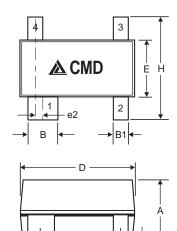
Another consideration is the output impedance of the power supply for fast transient currents. Most power supplies exhibit a much higher output impedance to fast transient current spikes. In the V_Z equation above, the V_{Supply} term, in reality, is given by $(V_{DC} + I_{esd} \times R_{out})$, where V_{DC} and R_{out} are the nominal supply DC output voltage and effective output impedance of the power supply respectively. As an example, a R_{out} of 1 ohm would result in a 10V increment in V_Z for a peak I_{esd} of 10A. To mitigate this effect, a high frequency bypass capacitor should be connected between the V_P pin of

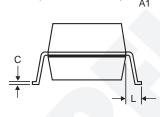


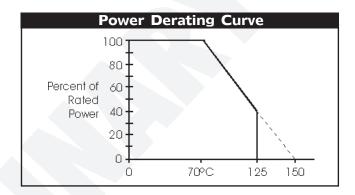
the PAC DN004 and the ground plane. The value of this bypass capacitor should be chosen such that it will absorb the charge transferred by the ESD pulse with minimal change in Vp. Typically a value in the $0.1\,\mu\text{F}$ to $0.2\,\mu\text{F}$ range is adequate for IEC-1000-4-2, level 4 contact discharge protection (8KV). Ceramic chip capacitors mounted with short printed circuit board traces are a good choice for this application. Electrolytic capacitors should be avoided as they have poor high frequency characteristics. For extra protection, connect a zener diode in parallel with the bypass capacitor to mitigate the effects of the parasitic series inductance inherent in the capacitor. The breakdown voltage of the zener diode should be slightly higher than the maximum supply voltage.

As a general rule, the PAC DN004 should be located as close as possible to the point of entry of expected electrostatic discharges. The power supply bypass capacitor mentioned above should be as close to the PAC DN004 as possible, with minimum PCB trace lengths to the power supply and ground planes to minimize stray series inductance.

SOT-143 - TOP VIEW







Mechanical Specifications			
Lead Plating	Tin-Lead		
Lead Material	Copper Alloy		
Lead Coplanarity	0.004" (0.102mm)		
Substrate Material	Silicon		
Body Material	Molded Epoxy		
Flammability	UL94V-0		

Package Dimensions, Power Dissipation & Information						
Package	SOT-143					
Pins	4					
	mm		inches			
	min	max	min	max		
Α	0.890	1.120	0.035	0.044		
A1	0.013	0.100	0.0005	0.004		
В	0.760	0.940	0.030	0.037		
B1	0.370	0.510	0.015	0.020		
С	0.0850	0.180	0.0033	0.0071		
D	2.800	3.040	0.110	0.120		
E	1.200	1.400	0.047	0.055		
e1	1.920 BSC		0.076 BSC			
e2	0.20 BSC		0.008 BSC			
Н	2.100	2.640	0.083	0.104		
L	0.55	ref	0.022 ref			
P _D @ 70 C	.225W					
# / bag	1000 pcs					
# / tape & reel	2,500 pcs					



(This page intentionally left blank)